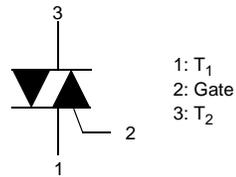
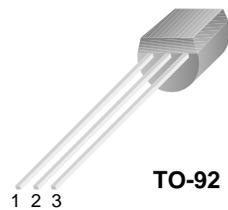


# FKN08PN40S

## TRIAC (Silicon Bidirectional Thyristor)

### Application Explanation

- Switching mode power supply, light dimmer, electric flasher unit, hair drier
- TV sets, stereo, refrigerator, washing machine
- Electric blanket, solenoid driver, small motor control
- Photo copier, electric tool



### Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Rating	Units
V <sub>DRM</sub> V <sub>RPM</sub>	Peak Repetitive Off-State Voltage	Sine Wave 50 to 60Hz, Gate Open	400	V
I <sub>T (RMS)</sub>	RMS On-State Current	Commercial frequency, sine full wave 360° conduction, T <sub>c</sub> = 70 °C	0.8	A
I <sub>TSM</sub>	Surge On-State Current	Sinewave half cycle, peak value, non-repetitive	60Hz 8	A
I <sup>2</sup> t	I <sup>2</sup> t for Fusing	Value corresponding to halfwave, surge on-state current, tp=8.33ms	0.26	A <sup>2</sup> s
P <sub>GM</sub>	Peak Gate Power Dissipation		5	W
P <sub>G (AV)</sub>	Average Gate Power Dissipation		0.1	W
V <sub>GM</sub>	Peak Gate Voltage		5	V
I <sub>GM</sub>	Peak Gate Current		1	A
T <sub>J</sub>	Junction Temperature		- 40 ~ 125	°C
T <sub>STG</sub>	Storage Temperature		- 40 ~ 125	°C

### Thermal Characteristics

Symbol	Parameter	Value	Units
R <sub>θJC</sub>	Thermal Resistance, Junction to Case <sup>(note1)</sup>	45	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient <sup>(note2)</sup>	160	°C/W

Note1: Infinite cooling condition.

Note2: JESD51-10 ( Test Borad: FR4 3.0"\*4.5"\*0.062", Minimum land pad)

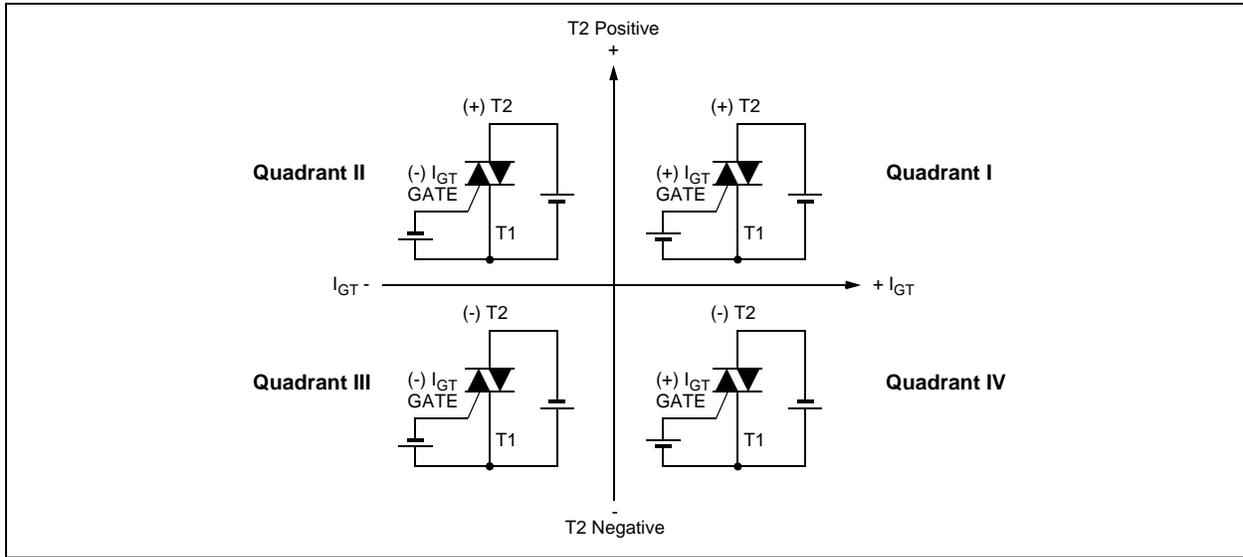
## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units		
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive Peak Off-State Current	V <sub>DRM</sub> /V <sub>RRM</sub> applied	-	-	100	μA		
V <sub>TM</sub>	On-State Voltage	T <sub>C</sub> =25°C, I <sub>TM</sub> =1.12A Instantaneous measurement	-	-	1.8	V		
V <sub>GT</sub>	Gate Trigger Voltage (Note 2)	I	V <sub>D</sub> =12V, R <sub>L</sub> =100Ω	T2(+), Gate (+)	-	-	2.0	V
		II		T2(+), Gate (-)	-	-	2.0	V
		III		T2(-), Gate (-)	-	-	2.0	V
I <sub>GT</sub>	Gate Trigger Current (Note 2)	I	V <sub>D</sub> =12V, R <sub>L</sub> =100Ω	T2(+), Gate (+)	-	-	5	mA
		II		T2(+), Gate (-)	-	-	5	mA
		III		T2(-), Gate (-)	-	-	5	mA
V <sub>GD</sub>	Gate Non-Trigger Voltage	T <sub>J</sub> =125°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.2	-	-	V		
I <sub>H</sub>	Holding Current (I, II, III)	V <sub>D</sub> = 12V, I <sub>TM</sub> = 200mA	-	-	15	mA		
I <sub>L</sub>	Latching Current	V <sub>D</sub> = 12V, I <sub>G</sub> = 10mA	I, III	-	-	15	mA	
			II	-	-	20	mA	
dv/dt(s)	Critical Rate of Rise of Off-State Voltage	V <sub>DRM</sub> = 63% Rated, T <sub>J</sub> = 125°C, Exponential Rise	20	-	-	V/μs		
dv/dt(c)	Critical-Rate of Rise of Off-State Commutating Voltage (di/dt=-0.7A/uS)		3.0	-	-	V/μs		

## Commutation dv/dt test

V <sub>DRM</sub> (V)	Test Condition	Commutating voltage and current waveforms (inductive load)
FKN08PN40S	<ol style="list-style-type: none"> <li>Junction Temperature T<sub>J</sub>=125°C</li> <li>Rate of decay of on-state commutating current (di/dt)<sub>C</sub></li> <li>Peak off-state voltage V<sub>D</sub> = 200V</li> </ol>	<p>The diagram shows three waveforms over time:         <ul style="list-style-type: none"> <li><b>Supply Voltage:</b> A sinusoidal wave.</li> <li><b>Main Current:</b> A sinusoidal wave that decays to zero during the commutation period. The rate of decay is labeled (di/dt)<sub>C</sub>.</li> <li><b>Main Voltage:</b> A square wave that rises to a peak V<sub>D</sub> during the commutation period. The rate of rise is labeled (dv/dt)<sub>C</sub>.</li> </ul> </p>

### Quadrant Definitions for a Triac

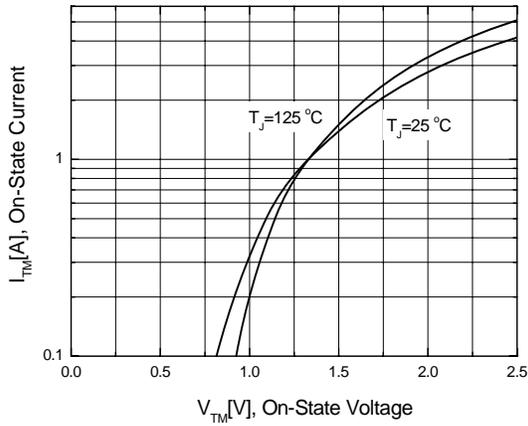


### Package Marking and Ordering Information

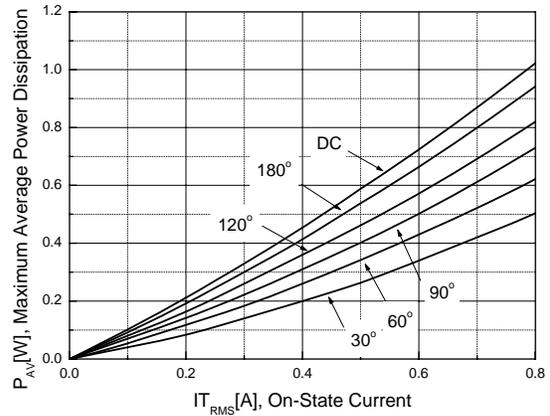
Device Marking	Device	Package	Packing	Tape Width	Quantity
K08PN40S	FKN08PN40S	TO-92	BULK	--	--

## Typical Performance Characteristics

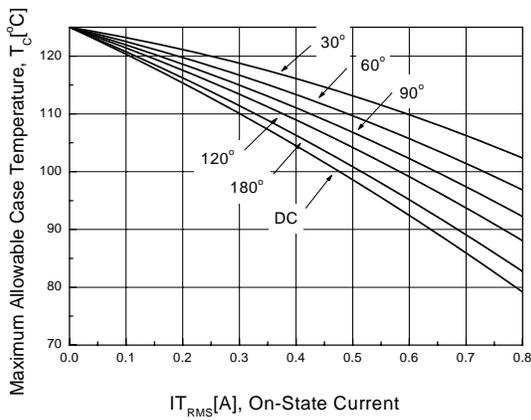
**Figure 1. On-State Characteristics**



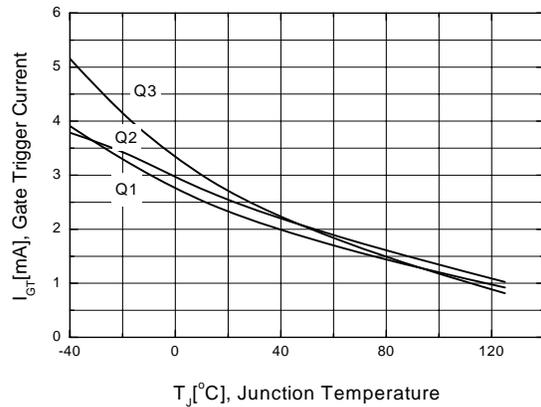
**Figure 2. Power Dissipation**



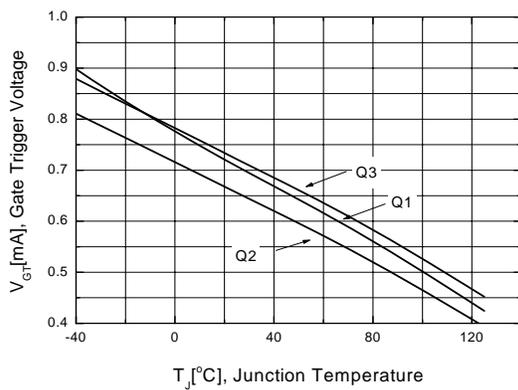
**Figure 3. RMS Current Rating**



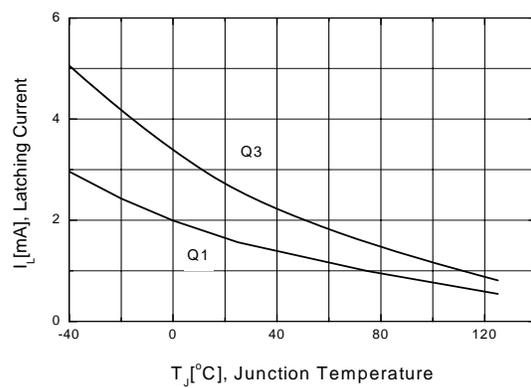
**Figure 4. Typical Gate Trigger Current vs Junction Temperature**



**Figure 5. Typical Gate Voltage vs Junction Temperature**

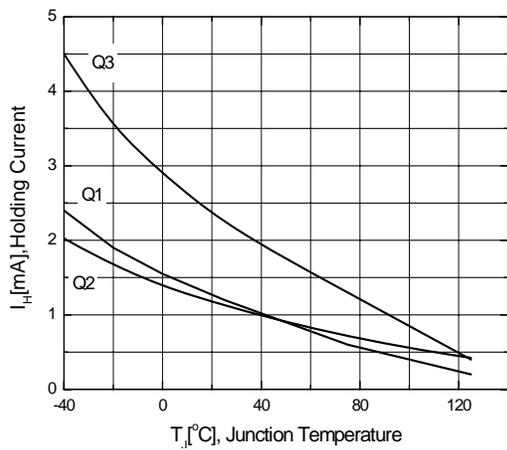


**Figure 6. Typical Latching Current vs Junction Temperature**

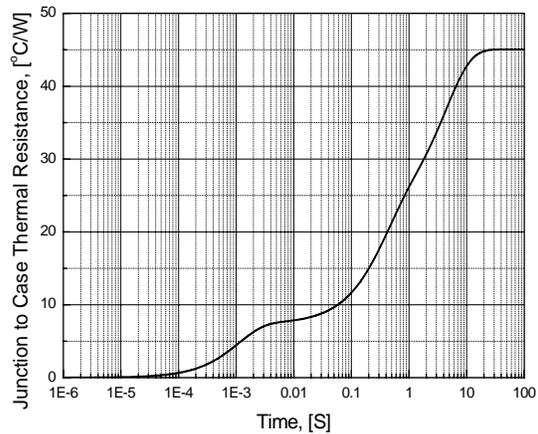


**Typical Performance Characteristics** (Continued)

**Figure7. Typical Holding Current vs Junction Temperature**

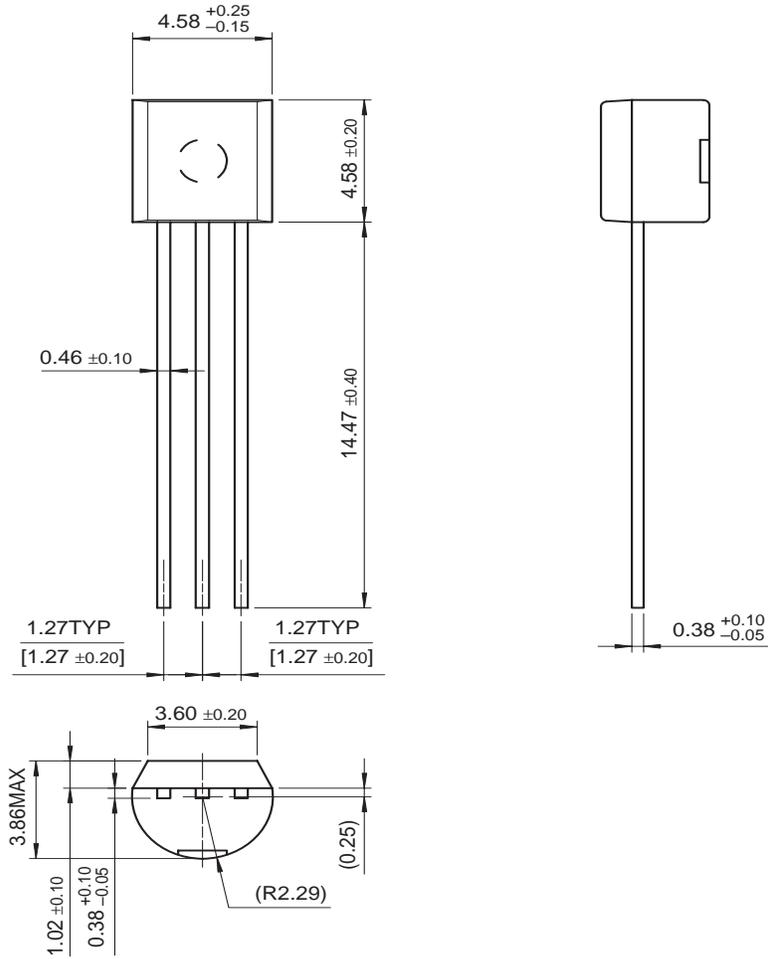


**Figure8. Junction to Case Thermal Resistance**



# Package Dimension

## TO-92





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| CorePLUSTM               | GTO™                 | Power-SPM™                 | The Power Franchise® |
| CROSSVOLT™               | i-Lo™                | PowerTrench®               | the power franchise  |
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